WAFER PRODUCING METHOD AND WAFER PRODUCING APPARATUS

ABSTRACT OF THE DISCLOSURE

A wafer producing method of producing a wafer from a hexagonal single crystal ingot, the method including a separation layer forming step of positioning a focal point of a laser beam of such a wavelength as to be transmitted through the hexagonal single crystal ingot at a depth corresponding to a thickness of a wafer to be produced from an end face of the hexagonal single crystal ingot and applying the laser beam to the hexagonal single crystal ingot to form a separation layer, an ultrasonic wave generating step of positioning an ultrasonic wave generating unit so as to face the wafer to be produced with a layer of water interposed therebetween and generating an ultrasonic wave through the layer of water to break down the separation layer, and a separation detecting step of detecting separation of the wafer to be produced from the hexagonal single crystal ingot according to change in sound.

[FIGURE 1]